

## High pressure studies on silane to 210 GPa at 300 K: optical evidence of an insulator–semiconductor transition

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## Erratum

### **High pressure studies on silane to 210 GPa at 300 K: optical evidence of an insulator–semiconductor transition**

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The glovebox which was used to load the silane into the diamond anvil cell has since been found to have had a faulty oxygen gauge. Thus the sample in the diamond anvil cell was not pure silane. We therefore withdraw all results and all conclusions in this paper. We apologize to readers and the journal staff.